

		4						
& TRAUE	ATTT	AL OF I	NFORMATION DISCLO	SURE STATEMENT		Docket No.		
TRANS	VIII I Z	U)	nder 37 CFR 1.97(b) or 1.97	(c))	1093	2-US		
In Po Ani	dication	Of: Luc	OUELLET, et al.					
III Ke Api	Jiloation	o Luc	, OOLLLLI, or a			Group Art Unit		
Serial No.			Filing Date	Examiner		2874		
09/833,711			13 April 2001			2014		
Title:	OPTICA	AL QUAL	ITY SILICA FILMS					
							3	
						- = =	)	
			Assistant Com	ddress to: missioner for Patents ton, D.C. 20231		0CT -4 200 2800 MAIL	7	
			.,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,			# + E	2	
1				FR 1.97 (b)		F 28	3	
1. 🖸	The In	formation	n Disclosure Statement submitt	ed herewith is being filed w	rithin thr ational s	ee months of the film tage as set forth in 3	ig 17	
	of a na	ational ap 1 491 in	an international application; of	before the mailing date of	of a firs	t Office A <del>cti</del> on on th	ie	
	merits	, whiche	ver event occurs last.					
				FR 1.97 (c)			20	
2. 🗖	The li	nformatio	on Disclosure Statement submit	tted herewith is being filed of the national stage as se	atter thr	in 37 CFR 1.491 in	er er	
			application, or the date of entry application; or after the mailing out before the mailing date of eight		tion on	(ne ments, wholes		
		1.	a Final Action under 37 CFF	R 1.113, or				
		2.	a Notice of Allowance unde	r 37 CFR 1.311,		7	7 5	
		which	never occurs first.			=		
	Also submitted herewith is:					, 3	$\sum_{i=1}^{\infty}$	
	<ul> <li>a certification as specified in 37 CFR 1.97(e);</li> </ul>					`	<u> </u>	
Ì			OR					
		the fee	e set forth in 37 CFR 1.17(p) 37 CFR 1.97(c).	for submission of an Info	ormation	n Disclosure Statem	ent	
-								



# TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT

(Under 37 CFR 1.97(b) or 1.97(c))

Docket No. 10932-US

In Re Application Of: Luc OUELLET, et al.

Serial No.	Filing Date	Examiner	Group Art Unit
09/833,711	13 April 2001		2874
09/655,711	13 April 2001		

Title: OPTICAL QUALITY SILICA FILMS

### Payment of Fee

- A check in the amount of is attached.

  The Assistant Commissioner is hereby authorized to charge and credit Deposit Account No. Charge the amount of Credit any overpayment.

  Charge the amount of Credit any overpayment.

  Charge any additional fee required.

  Certificate of Transmission by Facsimile\*

  Certificate of Mailling by Flora Commission by Facsimile Control of Mailling by Flora Control of Mailling by F

I certify that this document and authorization to charge deposit account is being facsimile transmitted to the United States Patent and Trademark Office (Fax. No. on (Date)

> Signature Typed pr Printed Name of Person Signing Certificate

\*This certificate may only be used if paying by

with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and addressed to the Assistant Commissioner for Patents, Washington, D.C. 20231.

Signature of Person Mailing Correspondence

Typed or Printed Name of Person Mailing Correspondence

deposit account.

Dated:

27 September 2002

Richard J. Mitchell

34.519 Marks & Clerk Canada

P.O. Box 957 Station B

Ottawa, ON, K1P 5S7

Phone: (613) 236-9561

10932-US APPLICANT(S) RMATION DISCLOSURE CITATION (Use several sheets if necessary) FILING DATE

SERIAL NO. ATTY DOCKET NO. 09/833,711 Luc OUELLET, et al. GROUP 2874 13 April 2001

### U.S. PATENT DOCUMENTS

U.S. PATENT DOCUMENTS							
'EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
INITIAL	4,394,401	July 19, 1983	Shioya et al.	427	39	August 7, 1981	
	5,904,491	May 18, 1999		438	31	April 23, 1997	
	5,979,188	November 9, 1999	Oiha	65	386	June 23, 1997	
	5,976,991	November 2, 1999	Laxman et al.	438	786	June 11, 1998	
	5,861,197	January 19, 1999		427	579	October 23, 1996	
	3,661,137	17.7					
		+				1 7	
						0 3	
						ا و د	
		+			+	0 8	
<b>!</b>						0	
	1	1					

### FOREIGN PATENT DOCUMENTS

FOREIGN FATERT BOODING.								
				LASS SUBCLASS		TRANSLATION		
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	YES	NO	
	0 935 284 A1		EP					
	0 624 660 A1		EP					
1								

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

- (1) "Stress in PSG and nitride films as related to film properties and annealing", T.H. Tom Wu et al., Solid State Technology, 35 (1992), No. 5, pages 65-72. (2) "Characteristics of low-temperature and low-energy plasma-enhanced chemical vapor deposited SiO2", J. Appl.Phys., Vol. 74, No. 4, 1993, pages 2638-2648.
  - (3) "Plasma-activated deposition and properties of phosphosilicate glass film", Akira Takamatsu et al., Journal of the Electrochemical Society, 1984, Vol. 131 No. 8, pages 1865-1870.
- (4) "Controlled oxidation of silane", K. Strater, RCA Electronic Components, pages 618-629. DATE CONSIDERED

EXAMINER

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy if this form with next communication to applicant.

Form PTO-1449